

Ilesanmi Adesida

List of Publications by Year in descending order

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43
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3610
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Elevated-Temperature Annealing Effects on AlGaIn/GaN Heterostructures. Journal of Electronic Materials, 2011, 40, 2344-2347. | 2.2 | 3 |
| 2 | Low resistance Mo/Al/Mo/Au ohmic contact scheme to InAlN/AlN/GaN heterostructure. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1538-1540. | 1.8 | 14 |
| 3 | Breakdown Voltage Enhancement of AlGaIn/GaN High-Electron-Mobility Transistors via Selective-Area Growth for Ohmic Contacts over Ion Implantation. Journal of Electronic Materials, 2010, 39, 499-503. | 2.2 | 14 |
| 4 | Fabrication of nanowires with high aspect ratios utilized by dry etching with SF ₆ :C ₄ F ₈ and self-limiting thermal oxidation on Si substrate. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, 763-768. | 1.2 | 13 |
| 5 | Direct contact mechanism of Ohmic metallization to AlGaIn/GaN heterostructures via Ohmic area recess etching. Applied Physics Letters, 2009, 95, . | 3.3 | 37 |
| 6 | Accumulation of fluorine in CF ₄ plasma-treated AlGaIn•GaN heterostructure interface: An experimental investigation. Journal of Applied Physics, 2009, 105, . | 2.5 | 15 |
| 7 | Recessed 70-nm Gate-Length AlGaIn/GaN HEMTs Fabricated Using an Al ₂ O ₃ /SiN _x Dielectric Layer. IEEE Electron Device Letters, 2009, 30, 913-915. | 3.9 | 9 |
| 8 | Ti/Al/Mo/Au Ohmic contacts to all-binary AlN/GaN high electron mobility transistors. Applied Physics Letters, 2008, 93, . | 3.3 | 20 |
| 9 | Formation mechanism of Ohmic contacts on AlGaIn•GaN heterostructure: Electrical and microstructural characterizations. Journal of Applied Physics, 2008, 103, . | 2.5 | 66 |
| 10 | Sub-Poissonian shot noise of a high internal gain injection photon detector. Optics Express, 2008, 16, 12701. | 3.4 | 34 |
| 11 | Study of fluorine bombardment on the electrical properties of AlGaIn•GaN heterostructures. Journal of Vacuum Science & Technology B, 2007, 25, 2607. | 1.3 | 14 |
| 12 | Nanometer-scale gaps in hydrogen silsesquioxane resist for T-gate fabrication. Journal of Vacuum Science & Technology B, 2007, 25, 2081. | 1.3 | 0 |
| 13 | Anatomy-performance correlation in Ti-based contact metallizations on AlGaIn•GaN heterostructures. Journal of Applied Physics, 2007, 101, 033708. | 2.5 | 33 |
| 14 | A photon detector with very high gain at low bias and at room temperature. Applied Physics Letters, 2007, 91, 171112. | 3.3 | 37 |
| 15 | Differences in the reaction kinetics and contact formation mechanisms of annealed Ti•Al•Mo•Au Ohmic contacts on n-GaN and AlGaIn•GaN epilayers. Journal of Applied Physics, 2007, 101, 013702. | 2.5 | 91 |
| 16 | Ohmic contacts to n ⁺ -GaN capped AlGaIn•AlN•GaN high electron mobility transistors. Applied Physics Letters, 2007, 91, . | 3.3 | 15 |
| 17 | Monolithic integration of thermally stable enhancement-mode and depletion-mode InAlAs/InGaAs/InP HEMTs utilizing Ir-gate and Ag-ohmic contact technologies. , 2006, , . | | 0 |
| 18 | The role of barrier layer on Ohmic performance of Ti•Al-based contact metallizations on AlGaIn•GaN heterostructures. Journal of Applied Physics, 2006, 100, 023708. | 2.5 | 47 |

| # | ARTICLE | IF | CITATIONS |
|----|---|------|-----------|
| 19 | Bendable GaN high electron mobility transistors on plastic substrates. Journal of Applied Physics, 2006, 100, 124507. | 2.5 | 157 |
| 20 | Printed Arrays of Aligned GaAs Wires for Flexible Transistors, Diodes, and Circuits on Plastic Substrates. Small, 2006, 2, 1330-1334. | 10.0 | 76 |
| 21 | Transfer printing by kinetic control of adhesion to an elastomeric stamp. Nature Materials, 2006, 5, 33-38. | 27.5 | 1,348 |
| 22 | Gigahertz operation in flexible transistors on plastic substrates. Applied Physics Letters, 2006, 88, 183509. | 3.3 | 67 |
| 23 | Ultralow resistance Si-containing Ti ⁺ Al ⁺ Mo ⁺ Au Ohmic contacts with large processing window for AlGa ⁺ N ⁺ GaN heterostructures. Applied Physics Letters, 2006, 88, 212107. | 3.3 | 28 |
| 24 | Process development for the realization of thermally-reliable enhancement-mode InAlAs/InGaAs/InP HEMTs with excellent DC and RF performance. , 2006, , . | | 1 |
| 25 | Properties of R.F. magnetron sputtered cadmium ⁺ oxide and indium ⁺ oxide thin films. Thin Solid Films, 2005, 479, 223-231. | 1.8 | 74 |
| 26 | Dislocation-induced nonuniform interfacial reactions of Ti ⁺ Al ⁺ Mo ⁺ Au ohmic contacts on AlGa ⁺ N ⁺ GaN heterostructure. Applied Physics Letters, 2005, 87, 141915. | 3.3 | 65 |
| 27 | Characterization of Au and Al segregation layer in post-annealed thin Ti ⁺ Al ⁺ Mo ⁺ Au Ohmic contacts to n ⁺ GaN. Journal of Applied Physics, 2005, 98, 106105. | 2.5 | 27 |
| 28 | Bendable GaAs metal-semiconductor field-effect transistors formed with printed GaAs wire arrays on plastic substrates. Applied Physics Letters, 2005, 87, 083501. | 3.3 | 70 |
| 29 | Noninterfacial-nitride formation ohmic contact mechanism in Si-containing Ti ⁺ Al ⁺ Mo ⁺ Au metallizations on AlGa ⁺ N ⁺ GaN heterostructures. Applied Physics Letters, 2005, 87, 262111. | 3.3 | 20 |
| 30 | Surface-state origin for the blueshifted emission in anodically etched porous silicon carbide. Journal of Applied Physics, 2004, 95, 490-496. | 2.5 | 73 |
| 31 | Comparative study of Ti ⁺ Al ⁺ Mo ⁺ Au, Mo ⁺ Al ⁺ Mo ⁺ Au, and V ⁺ Al ⁺ Mo ⁺ Au ohmic contacts to AlGa ⁺ N ⁺ GaN heterostructures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 2409. | 1.6 | 88 |
| 32 | Structural and spectroscopic characterization of porous silicon carbide formed by Pt-assisted electroless chemical etching. Solid State Communications, 2003, 126, 245-250. | 1.9 | 65 |
| 33 | Morphology evolution and luminescence properties of porous GaN generated via Pt-assisted electroless etching of hydride vapor phase epitaxy GaN on sapphire. Journal of Applied Physics, 2003, 94, 7526. | 2.5 | 44 |
| 34 | Morphology and luminescence of porous GaN generated via Pt-assisted electroless etching. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 2375. | 1.6 | 52 |
| 35 | In-plane bandgap control in porous GaN through electroless wet chemical etching. Applied Physics Letters, 2002, 80, 980-982. | 3.3 | 102 |
| 36 | Comparative study of self-aligned and nonself-aligned SiGe p-metal ⁺ oxide ⁺ semiconductor modulation-doped field effect transistors with nanometer gate lengths. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 3488. | 1.6 | 5 |

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|----|--|-----|-----------|
| 37 | InGaAs metal-semiconductor-metal photodetectors with a hybrid combination of transparent and opaque electrodes. Applied Physics Letters, 1997, 70, 3026-3028. | 3.3 | 8 |
| 38 | <title>Long-wavelength metal-semiconductor-metal photodetectors with transparent and opaque electrodes</title>., 1995, , . | | 4 |
| 39 | Etching characteristics of Al _x Ga _{1-x} As in (NH ₄) ₂ Sx solutions. Applied Physics Letters, 1992, 60, 1114-1116. | 3.3 | 24 |
| 40 | Fine line lithography using ion beams. Nuclear Instruments & Methods in Physics Research B, 1985, 7-8, 923-928. | 1.4 | 12 |
| 41 | The range of light ions in polymeric resists. Journal of Applied Physics, 1984, 56, 1801-1807. | 2.5 | 17 |
| 42 | Ion bombardment of resists. Nuclear Instruments & Methods in Physics Research, 1983, 209-210, 79-86. | 0.9 | 43 |
| 43 | Monte Carlo simulation of ion beam penetration in solids. Radiation Effects, 1982, 61, 223-233. | 0.4 | 46 |